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LM4250

Programmable Operational Amplifier

General Description

The LM4250 and LM4250C are extremely versatile programmable monolithic operational amplifiers. A single external master bias current setting resistor programs the input bias current, input offset current, quiescent power consumption, slew rate, input noise, and the gain-bandwidth product. The device is a truly general purpose operational amplifier.

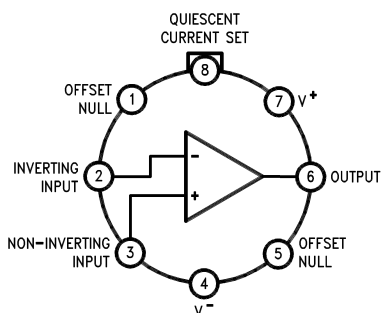
The LM4250C is identical to the LM4250 except that the LM4250C has its performance guaranteed over a 0°C to +70°C temperature range instead of the -55°C to +125°C temperature range of the LM4250.

Features

- $\pm 1\text{V}$ to $\pm 18\text{V}$ power supply operation
- 3 nA input offset current
- Standby power consumption as low as 500 nW
- No frequency compensation required
- Programmable electrical characteristics
- Offset voltage nulling capability
- Can be powered by two flashlight batteries
- Short circuit protection

Connection Diagrams

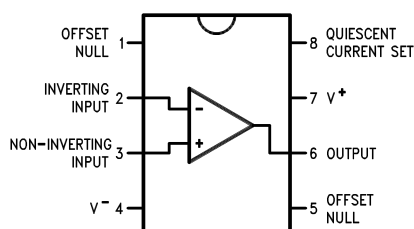
Metal Can Package



Top View

DS009300-2

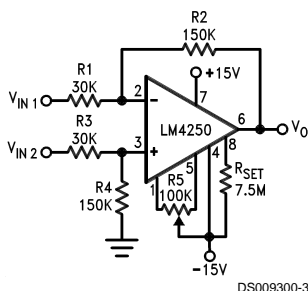
Dual-In-Line Package



Top View

DS009300-5

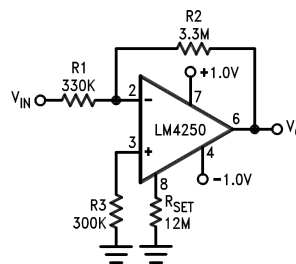
X5 Difference Amplifier



DS009300-3

Quiescent $P_D = 0.6 \text{ mW}$

500 Nano-Watt X10 Amplifier



DS009300-4

Quiescent $P_D = 500 \text{ nW}$

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

(Note 3)

	LM4250	LM4250C
Supply Voltage	$\pm 18\text{V}$	$\pm 18\text{V}$
Operating Temp. Range	$-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$	$0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$
Differential Input Voltage	$\pm 30\text{V}$	$\pm 30\text{V}$
Input Voltage (Note 2)	$\pm 15\text{V}$	$\pm 15\text{V}$
I_{SET} Current	150 nA	150 nA
Output Short Circuit Duration	Continuous	Continuous
T_{JMAX}		
H-Package	150°C	100°C
N-Package		100°C
J-Package	150°C	100°C
M-Package		100°C
Power Dissipation at $T_A = 25^{\circ}\text{C}$		
H-Package (Still Air)	500 mW	300 mW
(400 LF/Min Air Flow)	1200 mW	1200 mW
N-Package		500 mW
J-Package	1000 mW	600 mW
M-Package		350 mW
Thermal Resistance (Typical) θ_{JA}		
H-Package (Still Air)	165°C/W	165°C/W
(400 LF/Min Air Flow)	65°C/W	65°C/W
N-Package		130°C/W
J-Package	108°C/W	108°C/W
M-Package		190°C/W
(Typical) θ_{JC}		
H-Package	21°C/W	21°C/W
Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$	-65°C to $+150^{\circ}\text{C}$
Soldering Information		
Dual-In-Line Package		
Soldering (10 seconds)	260°C	
Small Outline Package		
Vapor Phase (60 seconds)	215°C	
Infrared (15 seconds)	220°C	

See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

ESD tolerance (Note 4) 800V

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.

Note 2: For supply voltages less than $\pm 15\text{V}$, the absolute maximum input voltage is equal to the supply voltage.

Note 3: Refer to RETS4250X for military specifications.

Note 4: Human body model, 1.5 k Ω in series with 100 pF.

Resistor Biasing

Set Current Setting Resistor to V^-

V_S	I_{SET}				
	0.1 μA	0.5 μA	1.0 μA	5 μA	10 μA
$\pm 1.5V$	25.6 M Ω	5.04 M Ω	2.5 M Ω	492 k Ω	244 k Ω
$\pm 3.0V$	55.6 M Ω	11.0 M Ω	5.5 M Ω	1.09 M Ω	544 k Ω
$\pm 6.0V$	116 M Ω	23.0 M Ω	11.5 M Ω	2.29 M Ω	1.14 M Ω
$\pm 9.0V$	176 M Ω	35.0 M Ω	17.5 M Ω	3.49 M Ω	1.74 M Ω
$\pm 12.0V$	236 M Ω	47.0 M Ω	23.5 M Ω	4.69 M Ω	2.34 M Ω
$\pm 15.0V$	296 M Ω	59.0 M Ω	29.5 M Ω	5.89 M Ω	2.94 M Ω

Electrical Characteristics

LM4250 ($-55^\circ C \leq T_A \leq +125^\circ C$ unless otherwise specified.) $T_A = T_J$

Parameter	Conditions	$V_S = \pm 1.5V$			
		$I_{SET} = 1 \mu A$		$I_{SET} = 10 \mu A$	
		Min	Max	Min	Max
V_{OS}	$R_S \leq 100 k\Omega$, $T_A = 25^\circ C$		3 mV		5 mV
I_{OS}	$T_A = 25^\circ C$		3 nA		10 nA
I_{bias}	$T_A = 25^\circ C$		7.5 nA		50 nA
Large Signal Voltage Gain	$R_L = 100 k\Omega$, $T_A = 25^\circ C$ $V_O = \pm 0.6V$, $R_L = 10 k\Omega$	40k		50k	
Supply Current	$T_A = 25^\circ C$		7.5 μA		80 μA
Power Consumption	$T_A = 25^\circ C$		23 μW		240 μW
V_{OS}	$R_S \leq 100 k\Omega$		4 mV		6 mV
I_{OS}	$T_A = +125^\circ C$ $T_A = -55^\circ C$		5 nA 3 nA		10 nA 10 nA
I_{bias}			7.5 nA		50 nA
Input Voltage Range		$\pm 0.6V$		$\pm 0.6V$	
Large Signal Voltage Gain	$V_O = \pm 0.5V$, $R_L = 100 k\Omega$ $R_L = 10 k\Omega$	30k		30k	
Output Voltage Swing	$R_L = 100 k\Omega$ $R_L = 10 k\Omega$	$\pm 0.6V$		$\pm 0.6V$	
Common Mode Rejection Ratio	$R_S \leq 10 k\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 k\Omega$	76 dB		76 dB	
Supply Current			8 μA		90 μA

Parameter	Conditions	$V_S = \pm 15V$			
		$I_{SET} = 1 \mu A$		$I_{SET} = 10 \mu A$	
		Min	Max	Min	Max
V_{OS}	$R_S \leq 100 k\Omega$, $T_A = 25^\circ C$		3 mV		5 mV
I_{OS}	$T_A = 25^\circ C$		3 nA		10 nA
I_{bias}	$T_A = 25^\circ C$		7.5 nA		50 nA
Large Signal Voltage Gain	$R_L = 100 k\Omega$, $T_A = 25^\circ C$ $V_O = \pm 10V$, $R_L = 10 k\Omega$	100k		100k	
Supply Current	$T_A = 25^\circ C$		10 μA		90 μA
Power Consumption	$T_A = 25^\circ C$		300 μW		2.7 mW
V_{OS}	$R_S \leq 100 k\Omega$		4 mV		6 mV
I_{OS}	$T_A = +125^\circ C$ $T_A = -55^\circ C$		25 nA 3 nA		25 nA 10 nA
I_{bias}			7.5 nA		50 nA
Input Voltage Range		$\pm 13.5V$		$\pm 13.5V$	

Electrical Characteristics (Continued)

Parameter	Conditions	$V_S = \pm 15V$			
		$I_{SET} = 1 \mu A$		$I_{SET} = 10 \mu A$	
		Min	Max	Min	Max
Large Signal Voltage Gain	$V_O = \pm 10V$, $R_L = 100 \text{ k}\Omega$ $R_L = 10 \text{ k}\Omega$	50k		50k	
Output Voltage Swing	$R_L = 100 \text{ k}\Omega$ $R_L = 10 \text{ k}\Omega$	$\pm 12V$		$\pm 12V$	
Common Mode Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	76 dB		76 dB	
Supply Current			11 μA		100 μA
Power Consumption			330 μW		3 mW

Electrical Characteristics

LM4250C ($0^\circ C \leq T_A \leq +70^\circ C$ unless otherwise specified.) $T_A = T_J$

Parameter	Conditions	$V_S = \pm 1.5V$			
		$I_{SET} = 1 \mu A$		$I_{SET} = 10 \mu A$	
		Min	Max	Min	Max
V_{OS}	$R_S \leq 100 \text{ k}\Omega$, $T_A = 25^\circ C$		5 mV		6 mV
I_{OS}	$T_A = 25^\circ C$		6 nA		20 nA
I_{bias}	$T_A = 25^\circ C$		10 nA		75 nA
Large Signal Voltage Gain	$R_L = 100 \text{ k}\Omega$, $T_A = 25^\circ C$ $V_O = \pm 0.6V$, $R_L = 10 \text{ k}\Omega$	25k		25k	
Supply Current	$T_A = 25^\circ C$		8 μA		90 μA
Power Consumption	$T_A = 25^\circ C$		24 μW		270 μW
V_{OS}	$R_S \leq 10 \text{ k}\Omega$		6.5 mV		7.5 mV
I_{OS}			8 nA		25 nA
I_{bias}			10 nA		80 nA
Input Voltage Range		$\pm 0.6V$		$\pm 0.6V$	
Large Signal Voltage Gain	$V_O = \pm 0.5V$, $R_L = 100 \text{ k}\Omega$ $R_L = 10 \text{ k}\Omega$	25k		25k	
Output Voltage Swing	$R_L = 100 \text{ k}\Omega$ $R_L = 10 \text{ k}\Omega$	$\pm 0.6V$		$\pm 0.6V$	
Common Mode Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	74 dB		74 dB	
Supply Current			8 μA		90 μA
Power Consumption			24 μW		270 μW

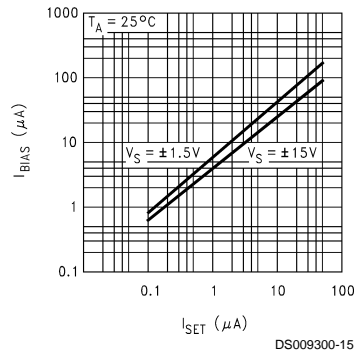
Parameter	Conditions	$V_S = \pm 15V$			
		$I_{SET} = 1 \mu A$		$I_{SET} = 10 \mu A$	
		Min	Max	Min	Max
V_{OS}	$R_S \leq 100 \text{ k}\Omega$, $T_A = 25^\circ C$		5 mV		6 mV
I_{OS}	$T_A = 25^\circ C$		6 nA		20 nA
I_{bias}	$T_A = 25^\circ C$		10 nA		75 nA
Large Signal Voltage Gain	$R_L = 100 \text{ k}\Omega$, $T_A = 25^\circ C$ $V_O = \pm 10V$, $R_L = 10 \text{ k}\Omega$	60k		60k	
Supply Current	$T_A = 25^\circ C$		11 μA		100 μA
Power Consumption	$T_A = 25^\circ C$		330 μW		3 mW
V_{OS}	$R_S \leq 100 \text{ k}\Omega$		6.5 mV		7.5 mV
I_{OS}			8 nA		25 nA
I_{bias}			10 nA		80 nA

Electrical Characteristics (Continued)

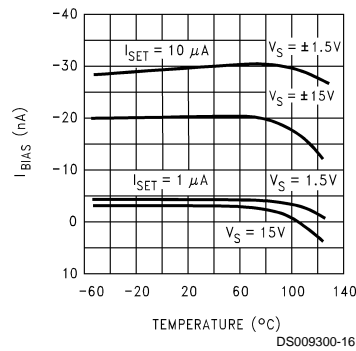
Parameter	Conditions	$V_S = \pm 15V$			
		$I_{SET} = 1 \mu A$		$I_{SET} = 10 \mu A$	
		Min	Max	Min	Max
Input Voltage Range		$\pm 13.5V$		$\pm 13.5V$	
Large Signal Voltage Gain	$V_O = \pm 10V, R_L = 100 k\Omega$	50k		50k	
Output Voltage Swing	$R_L = 100 k\Omega$ $R_L = 10 k\Omega$	$\pm 12V$		$\pm 12V$	
Common Mode Rejection Ratio	$R_S \leq 10 k\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 k\Omega$	74 dB		74 dB	
Supply Current			11 μA		100 μA
Power Consumption			330 μW		3 mW

Typical Performance Characteristics

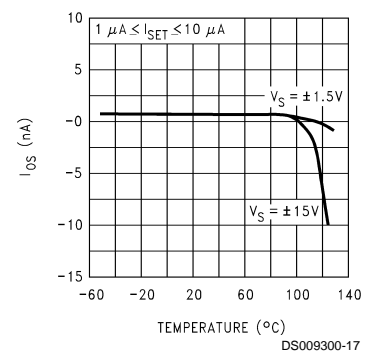
Input Bias Current vs I_{SET}



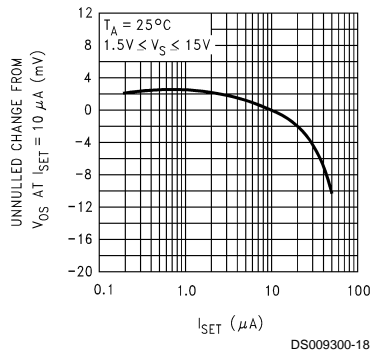
Input Bias Current vs Temperature



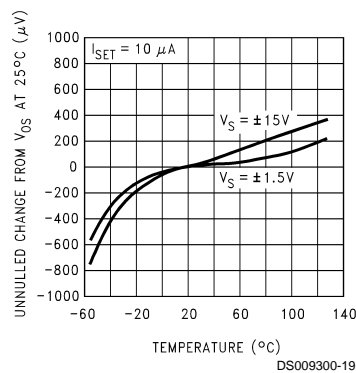
Input Offset Current vs Temperature



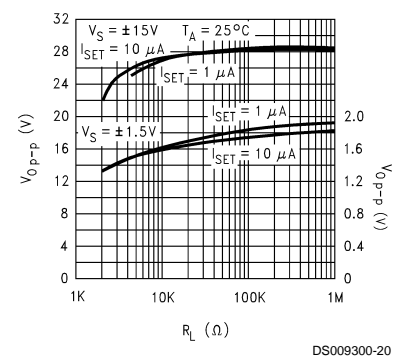
Unnull Input Offset Voltage Change vs I_{SET}



Unnull Input Offset Voltage Change vs Temperature

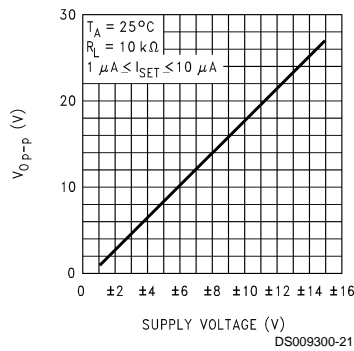


Peak to Peak Output Voltage Swing vs Load Resistance

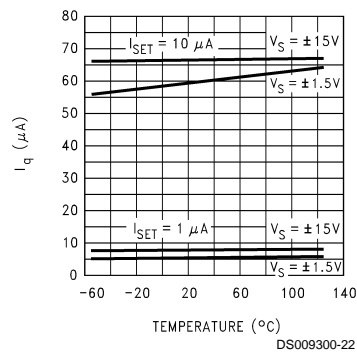


Typical Performance Characteristics (Continued)

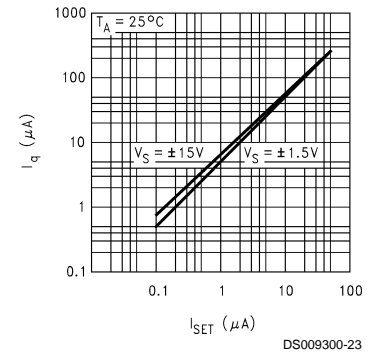
Peak to Peak Output Voltage Swing vs Supply Voltage



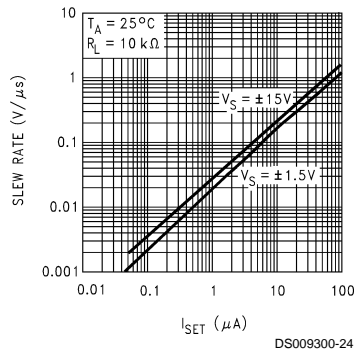
Quiescent Current (I_q) vs Temperature



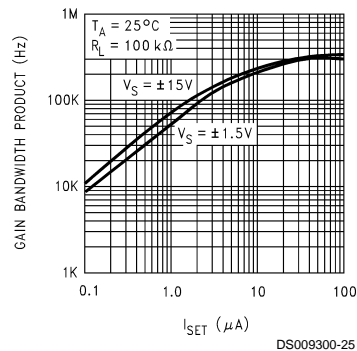
Quiescent Current (I_q) vs I_{SET}



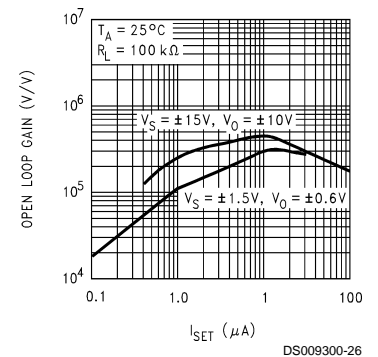
Slew Rate vs I_{SET}



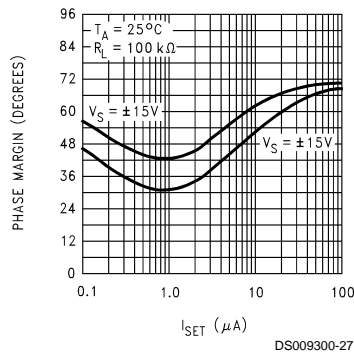
Gain Bandwidth Product vs I_{SET}



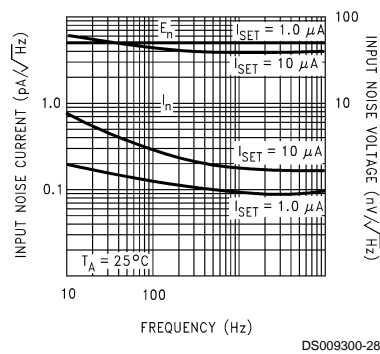
Open Loop Voltage Gain vs I_{SET}



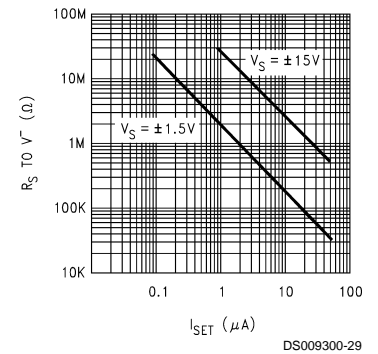
Phase Margin vs I_{SET}



Input Noise Current (I_n) and Voltage (E_n) vs Frequency

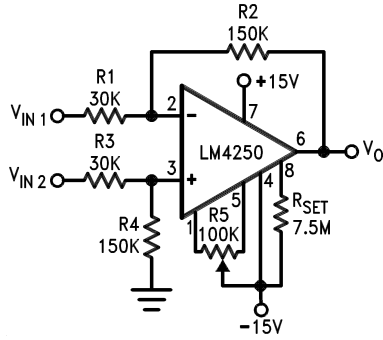


R_{SET} vs I_{SET}



Typical Applications

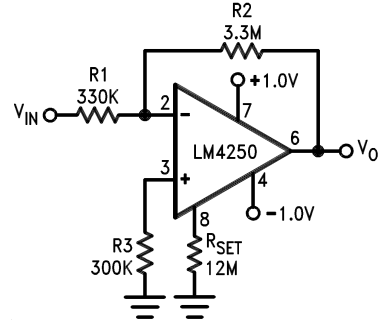
X5 Difference Amplifier



DS009300-3

Quiescent $P_D = 0.6 \text{ mW}$

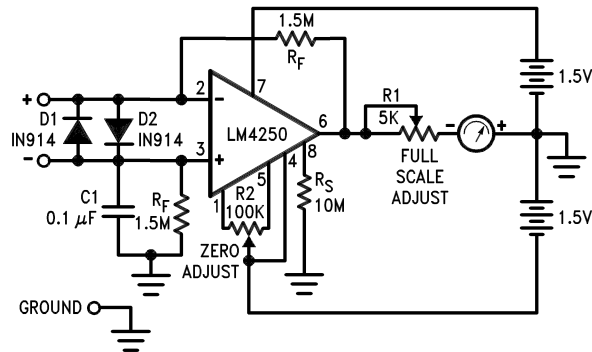
500 Nano-Watt X10 Amplifier



DS009300-4

Quiescent $P_D = 500 \text{ nW}$

**Floating Input Meter Amplifier
100 nA full Scale**



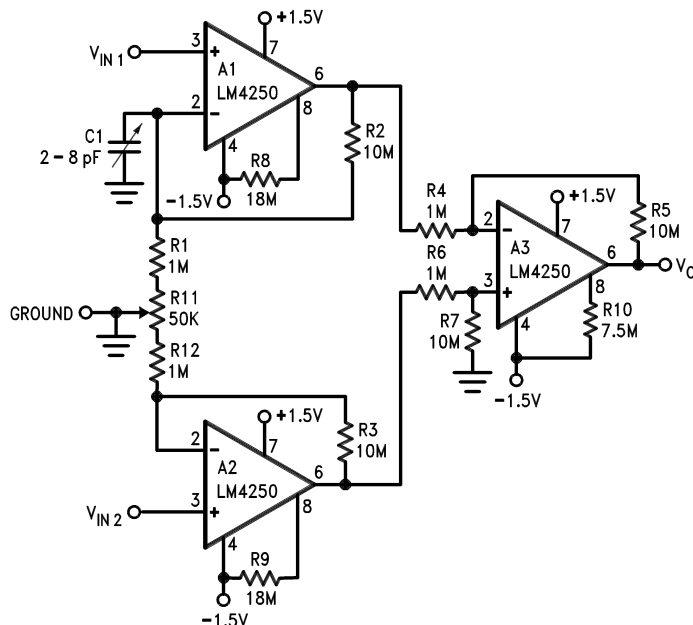
DS009300-8

Quiescent $P_D = 1.8 \text{ μW}$

*Meter movement (0–100 μA , 2 $\text{k}\Omega$) marked for 0–100 nA full scale.

Typical Applications (Continued)

X100 Instrumentation Amplifier 10 μ W



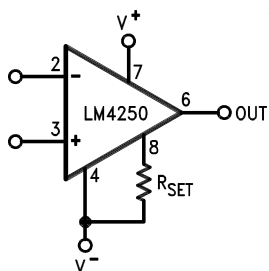
DS009300-9

Note 5: Quiescent $P_D = 10 \mu W$.

Note 6: R2, R3, R4, R5, R6 and R7 are 1% resistors.

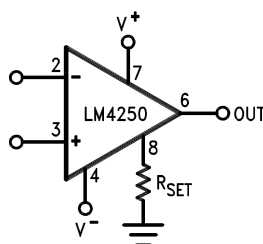
Note 7: R11 and C1 are for DC and AC common mode rejection adjustments.

R_{SET} Connected to V^-



DS009300-10

R_{SET} Connected to Ground



DS009300-11

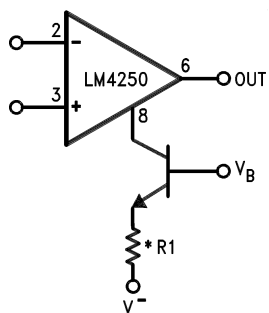
I_{SET} Equations:

$$I_{SET} \approx \frac{V^+ + |V^-| - 0.5}{R_{SET}} \quad \text{where } R_{SET} \text{ is connected to } V^-.$$

$$I_{SET} \approx \frac{V^+ - 0.5}{R_{SET}} \quad \text{where } R_{SET} \text{ is connected to ground.}$$

DS009300-30

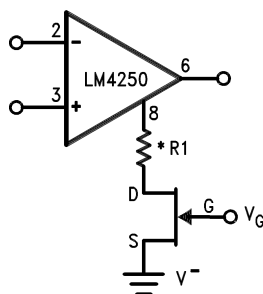
Transistor Current Sourcing Biasing



DS009300-12

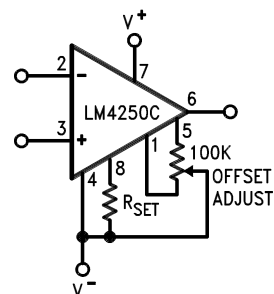
*R1 limits I_{SET} maximum

FET Current Sourcing Biasing



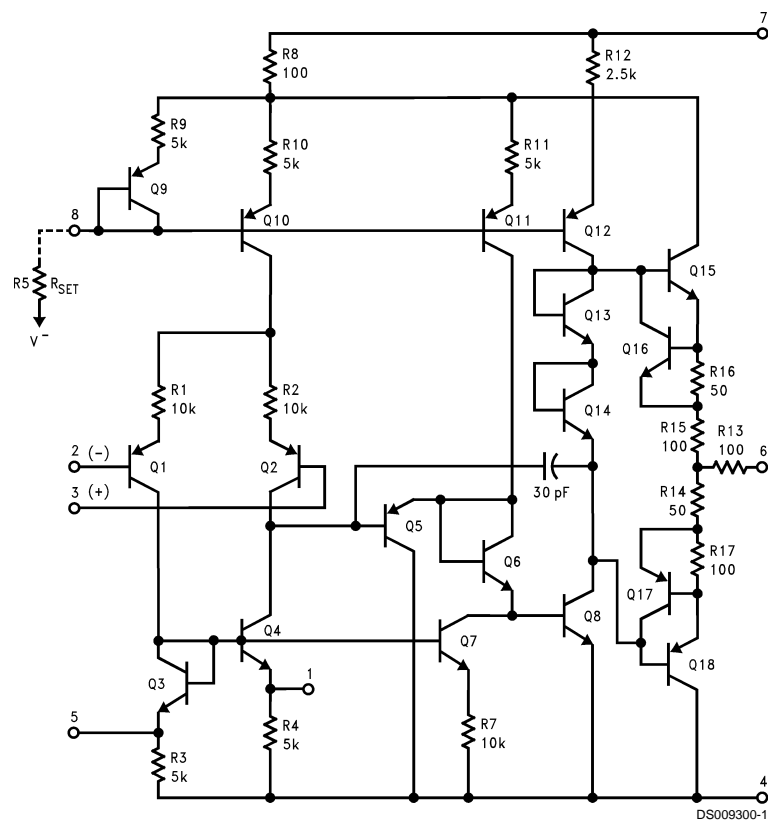
DS009300-13

Offset Null Circuit



DS009300-14

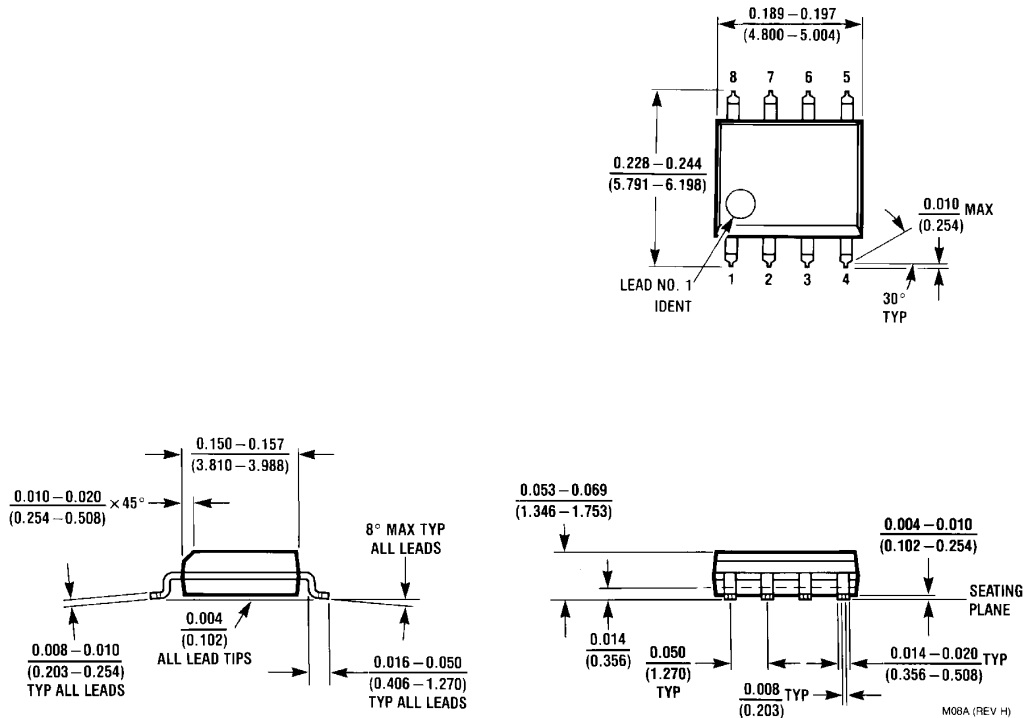
Schematic Diagram



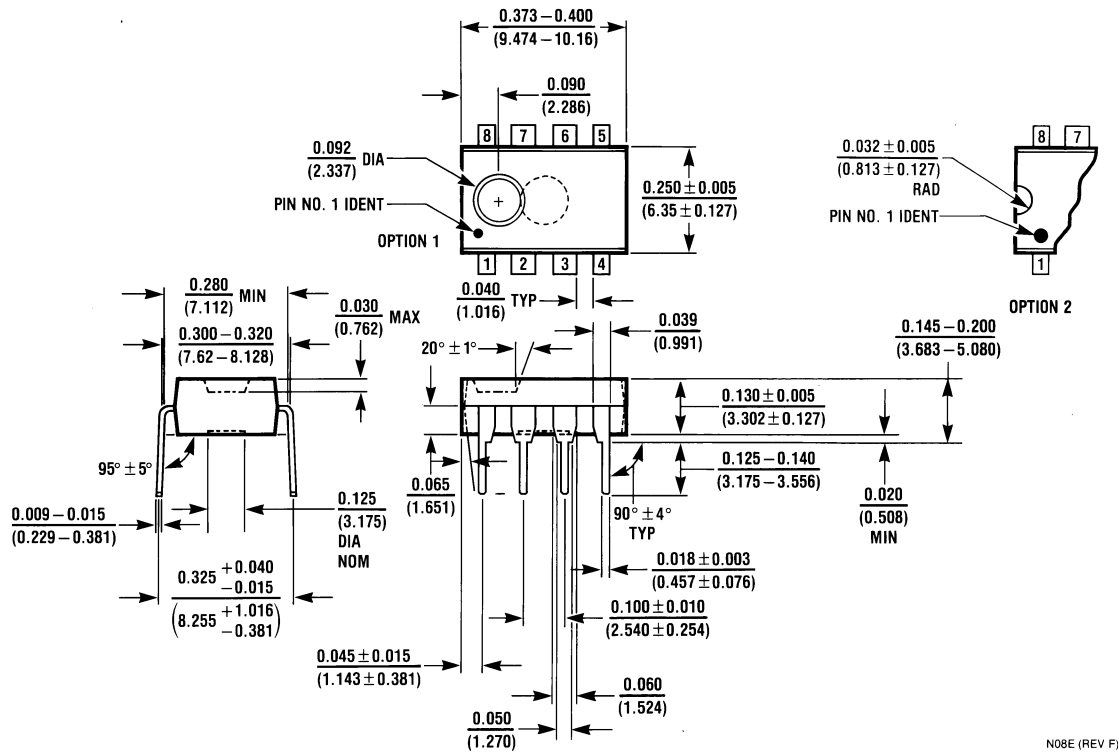
Ordering Information

Temperature Range		Package	NSC Package Number
Military -55°C ≤ T _A ≤ +125°C	Commercial 0°C ≤ T _A ≤ +70°C		
	LM4250CN	8-Pin Molded DIP	N08E
	LM4250CM LM4250CMX	8-Pin Surface Mount	M08A
LM4250J-MIL		8-Pin Ceramic DIP	J08E
	LM4250CH	8-Pin Metal Can	H08C

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



Small Outline Package (M)
Order Number LM4250CM or LM4250CMX
NS Package Number M08A



Molded Dual-In-Line Package (N)
Order Number LM4250CN
NS Package Number N08E

Notes

LIFE SUPPORT POLICY

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



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LM4250 Product Folder

Programmable Operational Amplifier

General Description	Features	Datasheet	Package & Models	Samples & Pricing	Design Tools	Application Notes
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Parametric Table

Channels (Channels)	1
Input Output Type	Not Rail to Rail
Bandwidth, typ (MHz)	.25
Slew Rate, typ (Volts/usec)	.20
Supply Current per Channel, typ (mA)	.01
Minimum Supply Voltage (Volt)	2

Parametric Table

Maximum Supply Voltage (Volt)	36
Offset Voltage, Max (mV)	6, 5
Input Bias Current, Temp Max (nA)	20
Output Current, typ (mA)	12
Voltage Noise, typ (nV/Hz)	40
Shut down	No
Special Features	Vos Adj, Adj Is

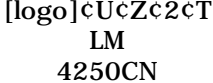
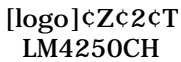
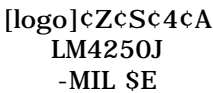
Datasheet

Title	Size in Kbytes	Date	<div></div> View Online	<div></div> Download	<div></div> Receive via Email
LM4250 Programmable Operational Amplifier	494 Kbytes	29-Aug-00	View Online	Download	Receive via Email
LM4250 Mil-Aero Datasheet MNLM4250-X	16 Kbytes		View Online	Download	Receive via Email

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Package Availability, Models, Samples & Pricing

Part Number	Package			Status	Models		Samples & Electronic Orders	Budgetary Pricing		Std Pack Size	Package Marking
	Type	Pins	MSL		SPICE	IBIS		Qty	\$US each		
LM4250CM	SOIC NARROW	8	MSL	Full production	LM4250.MOD	N/A	<div>24 Hour</div> <div>Buy Now</div>	1K+	\$0.4810	rail of 95	[logo]c2cT LM42 50CM
LM4250CMX	SOIC NARROW	8	MSL	Full production	LM4250.MOD	N/A	<div>Buy Now</div>	1K+	\$0.4810	reel of 2500	[logo]c2cT LM42 50CM

LM4250CN	MDIP	8	MSL	Full production	LM4250.MOD	N/A	Buy Now	1K+	\$0.4980	rail of 40	
LM4250CH	TO-5	8	MSL	Full production	LM4250.MOD	N/A	Buy Now	1K+	\$1.5200	box of 500	
LM4250C MWA	Wafer			Full production	LM4250.MOD	N/A				wafer jar of N/A	-
LM4250J-MIL	CERDIP	8	MSL	Full production	LM4250.MOD	N/A	Buy Now	50+	\$4.8300	rail of 40	
LM4250J MD8	Die			Full production	LM4250.MOD	N/A	Samples			tray of N/A	-
LM4250J MW8	Wafer			Full production	LM4250.MOD	N/A				wafer jar of N/A	-
LM4250C MDA	Die			Full production	LM4250.MOD	N/A	Samples			tray of N/A	-

General Description


The LM4250 and LM4250C are extremely versatile programmable monolithic operational amplifiers. A single external master bias current setting resistor programs the input bias current, input offset current, quiescent power consumption, slew rate, input noise, and the gain-bandwidth product. The device is a truly general purpose operational amplifier.

The LM4250C is identical to the LM4250 except that the LM4250C has its performance guaranteed over a 0°C to +70°C temperature range instead of the -55°C to +125°C temperature range of the LM4250.

Features

- ±1V to ±18V power supply operation
- 3 nA input offset current
- Standby power consumption as low as 500 nW
- No frequency compensation required
- Programmable electrical characteristics
- Offset voltage nulling capability
- Can be powered by two flashlight batteries
- Short circuit protection

Design Tools

Title	Size in Kbytes	Date	 View Online	 Download	 Receive via Email
Amplifiers Selection Guide software for Windows	7 Kbytes	12-Jun-2002	View		

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Application Notes

Title	Size in Kbytes	Date	<div></div> View Online	<div></div> Download	<div></div> Receive via Email
AN-71: Micropower Circuits Using the LM4250 Programmable Op Amp	195 Kbytes	4-Nov-95	View Online	Download	Receive via Email
LB-34: A Micropower Voltage Reference	74 Kbytes	28-Jun-96	View Online	Download	Receive via Email
AN-222: Application Note 222 Super Matched Bipolar Transistor Pair Sets New Standards for Drift and Noise	399 Kbytes	24-Feb-99	View Online	Download	Receive via Email
AN-88: Application Note 88 CMOS Linear Applications	87 Kbytes	24-Feb-99	View Online	Download	Receive via Email

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[Information as of 5-Aug-2002]